



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Atsushi YAGISHITA, et al.

Application No.: 10/023,849

Filed: December 21, 2001

For: SEMICONDUCTOR DEVICE (AS
AMENDED)

)

) Group Art Unit: 2822

) Examiner: Rose, Kiesha L.

)

)

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Sir:

AMENDMENT

In reply to the Office Action of March 31, 2003, with a period for response extending through June 30, 2003, please amend the application as follows. Applicants also respectfully request the Examiner's reconsideration in view of the following remarks:

IN THE DRAWINGS:

Submitted herewith is a Request for Approval of Drawing Changes in which proposed changes to Fig. 16X are indicated in red ink.

IN THE ABSTRACT:

Please replace the current Abstract with the Substitute Abstract attached on a separate page. The full text of the Abstract in clean form is as follows:

--There is provided a semiconductor device including a substrate, a device isolation insulating film formed on the substrate, a gate electrode formed on the substrate, a gate wiring

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